

## **CURRENT CLAIMS**

1. (Currently amended) A wafer having a surface, the wafer comprising:  
a plurality of regions of dielectric and polysilicon semiconductor [and dielectric]  
exposed at the surface of the wafer after chemical mechanical planarization,  
the semiconductor regions formed over a substrate, wherein  
the semiconductor regions have a total surface area that is less than or equal to a  
first fraction of a total surface area of the wafer and  
each of the semiconductor regions have a shortest surface dimension that is less  
than or equal to a first width,  
the first fraction and the first width ensuring that the surface of the wafer can  
attract enough water to wet sufficiently allowing removal of residual particles  
therefrom.
2. (Original) The wafer of claim 1 wherein the first fraction equals 60%.
3. (Original) The wafer of claim 1 wherein the first fraction equals 50%.
4. (Original) The wafer of claim 1 wherein the first width equals 2.5 millimeters.
5. (Original) The wafer of claim 1 wherein the first width equals 500 microns.
6. (Cancelled)
7. (Original) The wafer of claim 1 wherein the dielectric regions comprise silicon  
dioxide.
8. (Original) The wafer of claim 1 wherein the regions of dielectric and semiconductor  
alternate along the surface of the wafer.
9. (Original) The wafer of claim 1 wherein the regions of dielectric are elongated strips.

10. (Original) The wafer of claim 1 wherein the regions of semiconductor are elongated strips.

11. (Original) The wafer of claim 1 wherein the regions of dielectric are rectangular.

12. (Original) The wafer of claim 1 wherein the regions of semiconductor are rectangular.

13. (Original) The wafer of claim 1 wherein the regions of semiconductor are hexagonal.

14. (Original) The wafer of claim 1 wherein the regions of semiconductor are interspersed within a sea of dielectric.

15-29. (Cancelled)

30. (Currently amended) A wafer having a surface, the wafer comprising:  
means for attracting water to the surface of the wafer; and  
means for repelling water from the surface of the wafer comprising polysilicon  
regions above a substrate that have a combined surface area that is less than or  
equal to a first fraction of a surface area of the wafer,  
wherein each of the regions has a shortest surface dimension that is less than or  
equal to a first width, and the first fraction and the first width ensure that the  
surface of the wafer can attract enough water to wet sufficiently allowing  
removal of residual particles therefrom.

31. (Original) The wafer of claim 30 wherein the first fraction equals 60%.

32. (Original) The wafer of claim 30 wherein the first fraction equals 50%.

33. (Original) The wafer of claim 30 wherein the first width equals 2.5 millimeters.

34. (Original) The wafer of claim 30 wherein the first width equals 500 microns.

35. (Cancelled)

36. (Original) The wafer of claim 30 wherein the means for attracting water comprises silicon dioxide.

37. (Original) The wafer of claim 30 wherein the means for attracting water comprises elongated strips of dielectric.

38. (Original) The wafer of claim 30 wherein the means for attracting water comprises of rectangular regions of dielectric.

39. (Original) The wafer of claim 30 wherein the means for attracting water comprises dielectric regions, the means for repelling water comprises semiconductor regions, and wherein the dielectric regions and semiconductor regions alternate along the surface of the wafer.

40. (Original) The wafer of claim 30 wherein the means for repelling water comprises elongated strips of semiconductor.

41. (Original) The wafer of claim 30 wherein the means for repelling water comprises rectangular regions of semiconductor.

42. (Original) The wafer of claim 30 wherein the means for repelling water comprises hexagonal regions of semiconductor.

43. (Original) The wafer of claim 30 wherein the means for attracting water comprises dielectric, the means for repelling water comprises semiconductor regions, and the semiconductor regions are interspersed within a sea of dielectric.

44. (Currently amended) A wafer having a surface, the wafer comprising:  
a plurality of regions of polysilicon hydrophobic material and hydrophilic  
material exposed at the surface of the wafer after chemical mechanical  
planarization, wherein the regions of hydrophobic material are deposited over  
a substrate and have a total surface area that is less than or equal to a first  
fraction of a total surface area of the wafer, and each of the regions of  
hydrophobic material have a shortest surface dimension that is less than or  
equal to a first width, the first fraction and the first width ensuring that the  
surface of the wafer can attract enough water to wet sufficiently allowing  
removal of residual particles therefrom.

45. (Original) The wafer of claim 44 wherein the first fraction equals 60%.

46. (Original) The wafer of claim 44 wherein the first fraction equals 50%.

47. (Original) The wafer of claim 44 wherein the first width equals 2.5 millimeters.

48. (Original) The wafer of claim 44 wherein the first width equals 500 microns.

49. (Cancelled)

50. (Original) The wafer of claim 44 wherein the hydrophilic material comprises silicon  
dioxide.

51. (Original) The wafer of claim 44 wherein the regions of hydrophobic material and  
hydrophilic material alternate along the surface of the wafer.

52. (Original) The wafer of claim 44 wherein the regions of hydrophilic material and  
hydrophobic material are elongated strips.

53. (Original) The wafer of claim 44 wherein the regions of hydrophilic material are rectangular.

54. (Original) The wafer of claim 44 wherein the regions of hydrophobic material are rectangular.

55. (Original) The wafer of claim 44 wherein the regions of hydrophobic material are hexagonal.

56. (Original) The wafer of claim 44 wherein the regions of hydrophobic material are interspersed within a sea of hydrophilic material.

57. (New) The wafer of claim 1 wherein the polysilicon semiconductor regions comprise doped polysilicon.

58. (New) The wafer of claim 57 wherein the doped polysilicon is doped by depositing a dopant along with the polysilicon.

59. (New) The wafer of claim 30 wherein the means for repelling water from the surface comprise doped polysilicon.

60. (New) The wafer of claim 59 wherein the doped polysilicon is doped by depositing a dopant along with the polysilicon.

61. (New) The wafer of claim 44 wherein the polysilicon hydrophobic material comprises doped polysilicon.

62. (New) The wafer of claim 61 wherein the doped polysilicon is doped by depositing a dopant along with the polysilicon.